

N-channel MOSFET

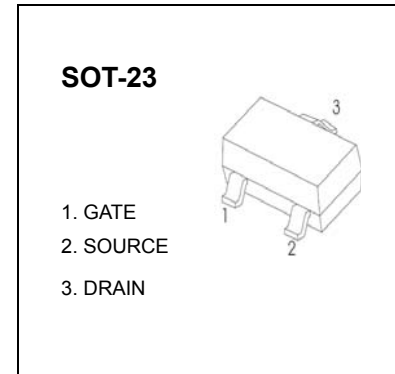
### FEATURES

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel
- **Pb-Free package is available**  
RoHS product for packing code suffix "G"  
Halogen free product for packing code suffix "H"

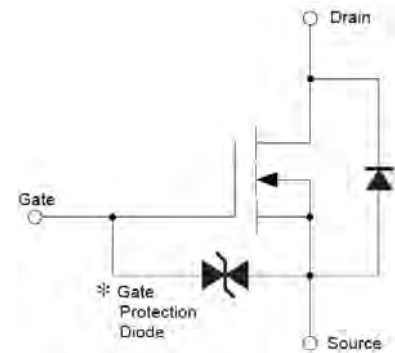
Marking: KN

### MOSFET MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	0.1	A
P <sub>D</sub>	Power Dissipation	0.35	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	357	°C/W



### Equivalent circuit



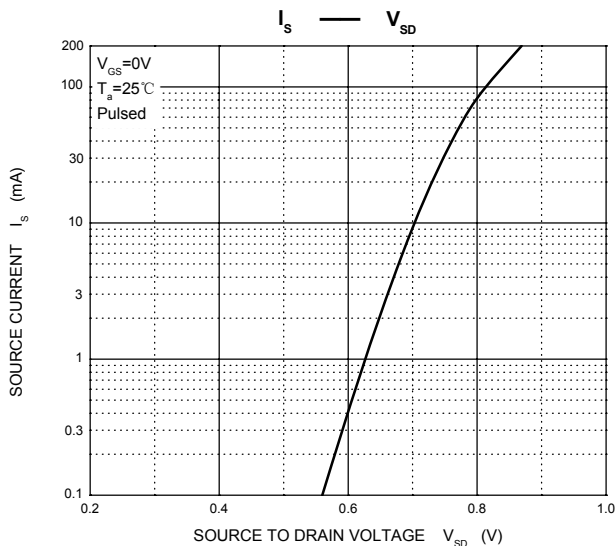
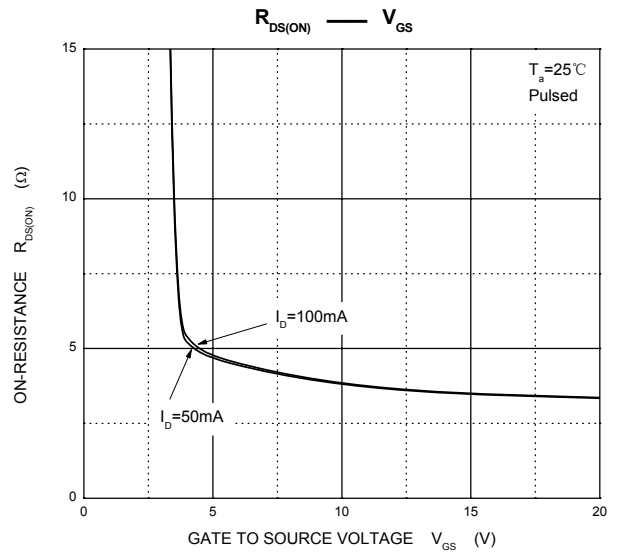
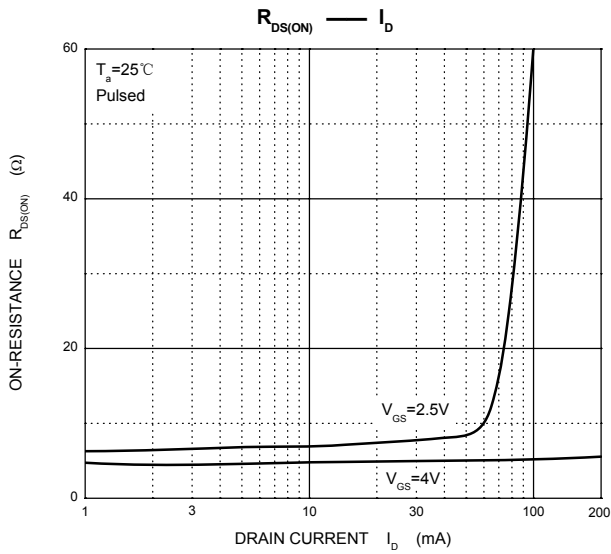
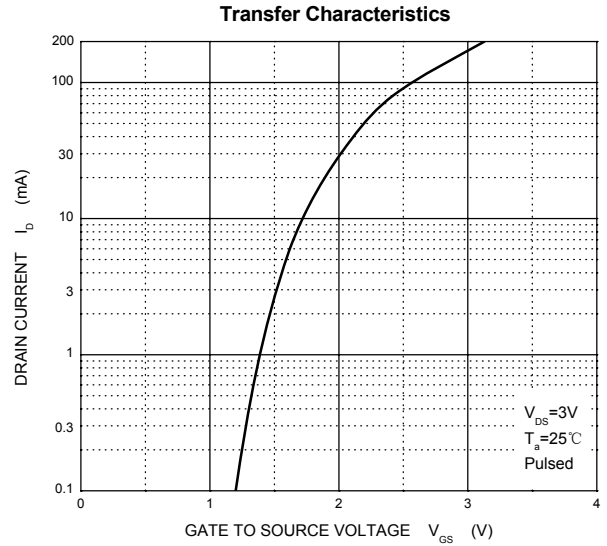
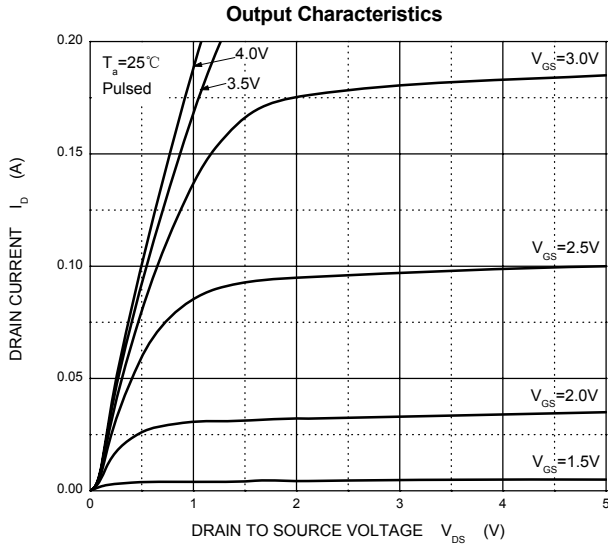
### MOSFET ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			0.2	μA
Gate -Source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±500	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 100μA	0.8		1.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4V, I <sub>D</sub> = 10mA			8	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1mA			13	Ω
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	20			mS
<b>Dynamic Characteristics*</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			4		pF
<b>Switching Characteristics*</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 5V, V <sub>DD</sub> = 5V, I <sub>D</sub> = 10mA, R <sub>G</sub> = 10Ω, R <sub>L</sub> = 500Ω,		15		ns
Rise Time	t <sub>r</sub>			35		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			80		ns
Fall Time	t <sub>f</sub>			80		ns

\* These parameters have no way to verify.



### Typical Characteristics

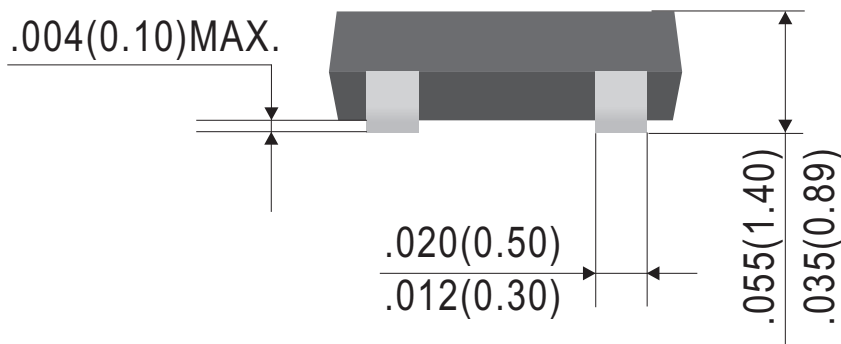
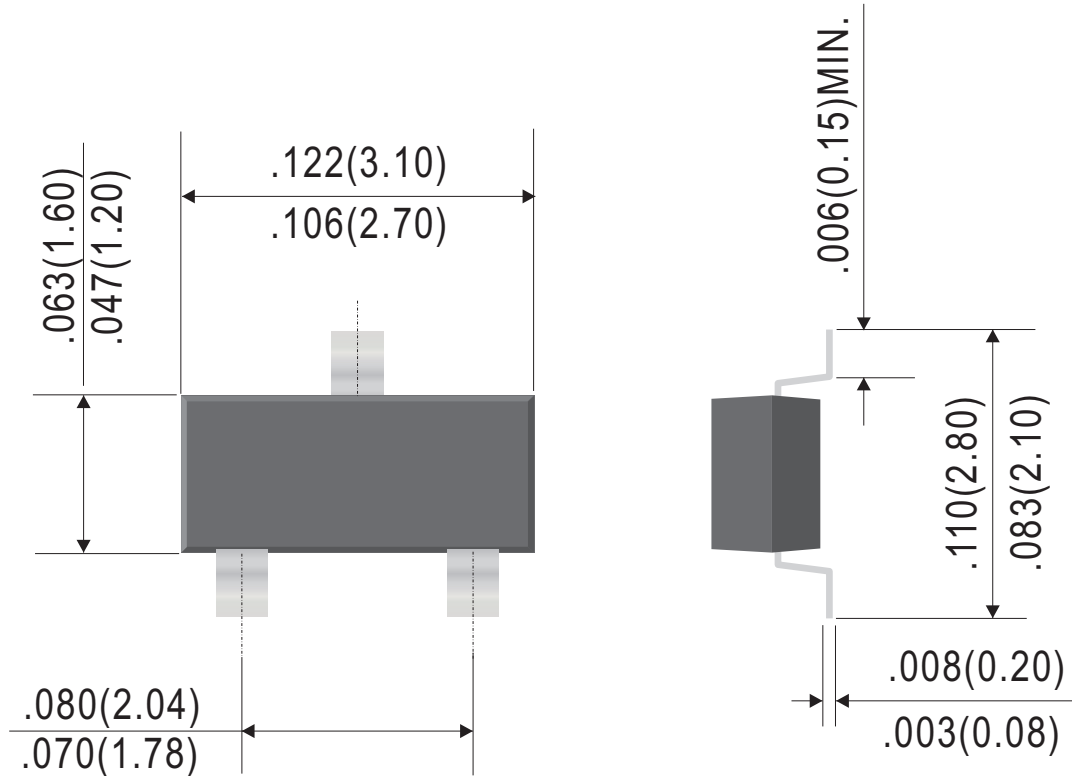




## SOT-23 Plastic-Encapsulate MOSFETS

### Outline Drawing

### SOT-23



Dimensions in inches and (millimeters)

**Ordering Information:**

Device PN	Packing
2SK3018LT1G <sup>(1)</sup> -WS	Tape&Reel: 3 Kpcs/Reel

Note: (1) RoHS product for packing code suffix "G" ; Halogen free product for packing code suffix "H"

**\*\*\*Disclaimer\*\*\***

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